

## Product Overview

### NCP5181: MOSFET / IGBT Drivers, High Voltage, High and Low Side, Dual Input

For complete documentation, see the data sheet.



The NCP5181 is a High Voltage Power Mosfet Driver providing two outputs for direct drive of a 2 N-channel power Mosfets arranged in a half-bridge (or any other high side + low side configuration). It uses the bootstrap technique to insure a proper drive of the High side power switch. The driver works with 2 independent inputs to accommodate any topology (including half-bridge, asymmetrical half-bridge, active clamp and full bridge).

### Features

- High Voltage Range: up to 600 V
  - dV/dt Immunity 50 V/nsec
  - Gate Drive Supply Range from 10 V to 20 V
  - High and Low DRV Outputs
  - Output Source / Sink Current Capability 1.1 A / 2.4 A
  - 3.3 V and 5 V Input Logic Compatible
  - Up to Vcc Swing on Input Pins
  - Matched Propagation Delays between Both Channels
  - Outputs in Phase with the Inputs
  - Independent Logic Inputs to Accommodate All Topologies
- For more features, see the data sheet

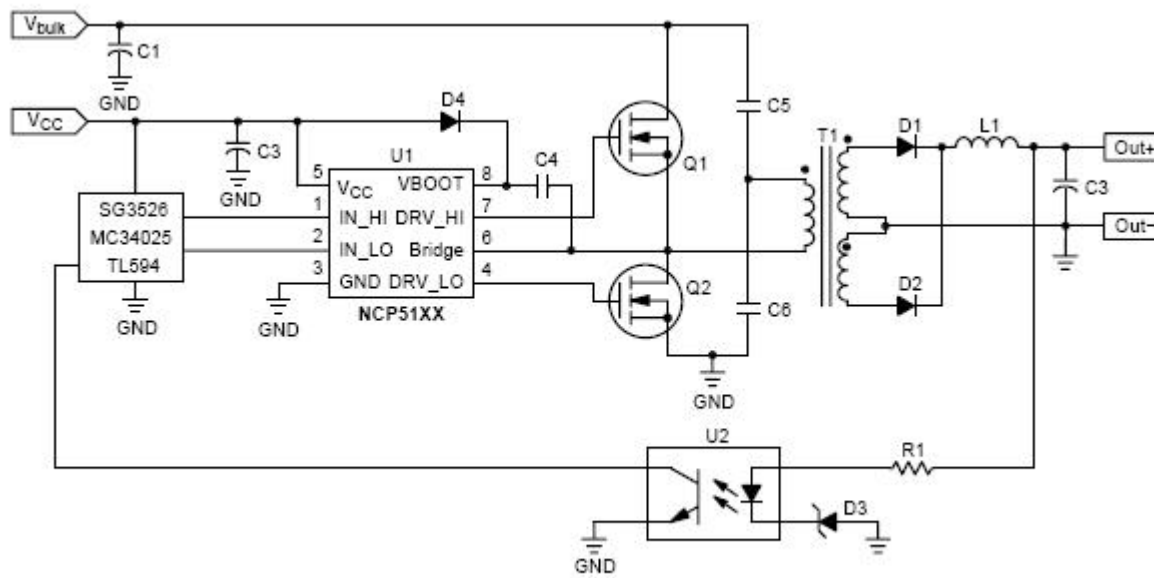
### Applications

- Bridge Inverter for UPS systems
- High Power Energy Management
- Half-bridge Power Converters
- Full-bridge Converters
- Any Complementary Drive Converters (asymmetrical halfbridge, active clamp)

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Power Switch	Number of Outputs	Topology	Isolation Type	V <sub>in</sub> Max (V)	V <sub>cc</sub> Max (V)	Drive Source / Sink Typ (mA)	Rise Time (ns)	Fall Time (ns)	t <sub>p</sub> Max (ns)	Package Type
NCP5181DR2G	0.9333	Pb-free Halide free non AEC-Q and PPAP	Active	MOSFET	2	High-Low	Junction Isolation	600	20	1400 / 2200	40	40	170	SOIC-8
NCP5181PG	1.378	Pb-free Halide free non AEC-Q and PPAP	Active	MOSFET	2	High-Low	Junction Isolation	600	20	1400 / 2200	20	20	170	PDIP-8

## Application Diagram



Typical Application

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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